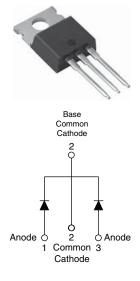
Vishay Semiconductors

### HEXFRED<sup>®</sup>, Ultrafast Soft Recovery Diode, 2 x 4 A



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#### TO-220AB

PRODUCT SUMMARY						
Package	TO-220AB					
I <sub>F(AV)</sub>	2 x 4 A					
V <sub>R</sub>	600 V					
V <sub>F</sub> at I <sub>F</sub>	1.8 V					
t <sub>rr</sub> (typ.)	17 ns					
T <sub>J</sub> max.	150 °C					
Diode variation	Common cathode					

#### FEATURES

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level

#### BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

#### DESCRIPTION

VS-HFA08TA60CPbF is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 600 V and 4 A per leg continuous current, the VS-HFA08TA60CPbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>RRM</sub>) and does not exhibit any tendency to "snap-off" during the  $t_{\rm b}$  portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TA60CPbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Cathode to anode voltage	V <sub>R</sub>		600	V		
Maximum continuous forward current	1	T <sub>C</sub> = 100 °C	4			
per device	- I <sub>F</sub>	$1_{\rm C} = 100$ C	8	А		
Single pulse forward current	I <sub>FSM</sub>		25	A		
Maximum repetitive forward current	I <sub>FRM</sub>		16			
Maximum neuror dissinction	р	T <sub>C</sub> = 25 °C	25	W		
Maximum power dissipation	PD	T <sub>C</sub> = 100 °C	10	٧V		
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to + 150	°C		

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Document Number: 94043

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e3 BoHS

COMPLIANT





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<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS	
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA		600	-	-		
		I <sub>F</sub> = 4.0 A		-	1.5	1.8	v	
Maximum forward voltage	$V_{FM}$	I <sub>F</sub> = 8.0 A	See fig. 1	-	1.8	2.2		
		I <sub>F</sub> = 4.0 A, T <sub>J</sub> = 125 °C		-	1.4	1.7		
Maximum reverse		V <sub>R</sub> = V <sub>R</sub> rated	Coofin 0	-	0.17	3.0		
leakage current	I <sub>RM</sub>	$T_J = 125 \text{ °C}, V_R = 0.8 \text{ x } V_R \text{ rated}$	See fig. 2	-	44	300	μA	
Junction capacitance	CT	V <sub>R</sub> = 200 V	See fig. 3	-	4.0	8.0	pF	
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from body	package	-	8.0	-	nH	

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	0 A/µs, V <sub>R</sub> = 30 V	-	17	-			
Reverse recovery time See fig. 5, 6 and 16	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	28	42	ns		
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	38	57			
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	2.9	5.2	А		
See fig. 7 and 8	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 4.0 A	-	3.7	6.7	~		
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C	dl <sub>F</sub> /dt = 200 A/µs	-	40	60	nC		
See fig. 9 and 10	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C	V <sub>R</sub> = 200 V	-	70	105	no		
Peak rate of fall of recovery current during t <sub>b</sub>	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	280	-	A∕µs		
See fig. 11 and 12	dl <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	235	-	λγµs		

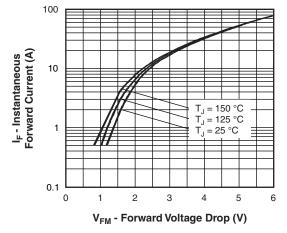
THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS			MAX.	UNITS		
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	5.0			
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	80	K/W		
Thermal resistance, case to heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-			
Weight			-	2.0	-	g		
weight			-	0.07	-	oz.		
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)		
Marking device		Case style TO-220AB		HFA08TA60C				

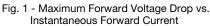
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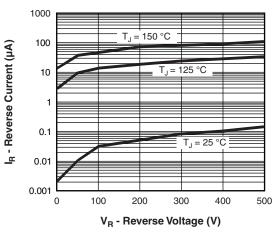
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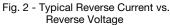


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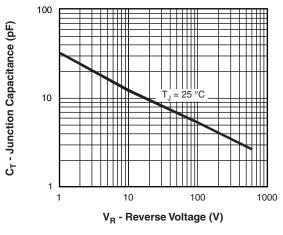
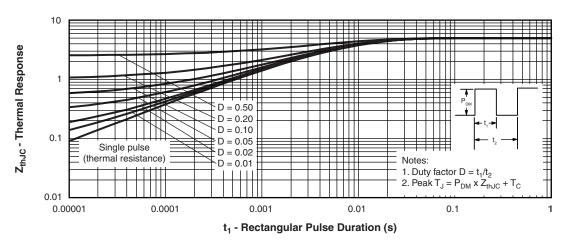


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





Revision: 23-May-11	3	Document Number: 94043
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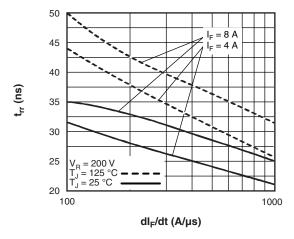


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

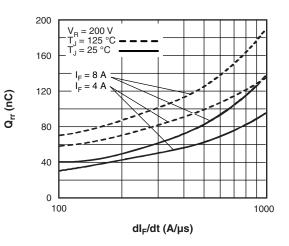


Fig. 7 - Typical Stored Charge vs.  $dI_F/dt$ 

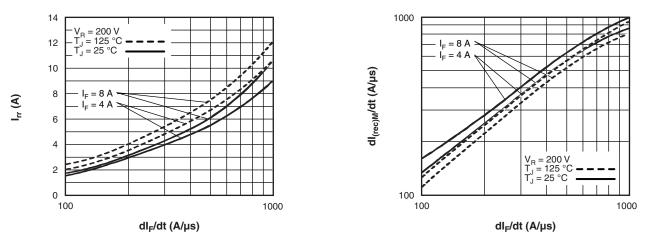


Fig. 6 - Typical Recovery Current vs. dI<sub>F</sub>/dt

Fig. 8 - Typical dl<sub>(rec)M</sub>/dt vs. dl<sub>F</sub>/dt



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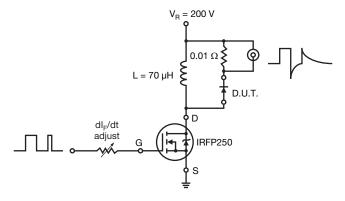


Fig. 9 - Reverse Recovery Parameter Test Circuit

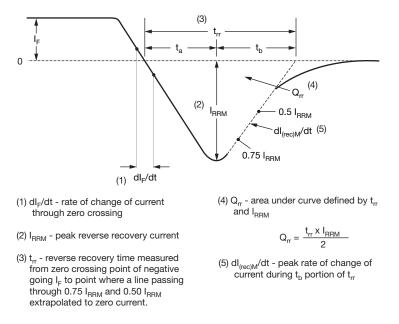


Fig. 10 - Reverse Recovery Waveform and Definitions

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#### **ORDERING INFORMATION TABLE**

Device code	VS-	HF	Α	08	ТА	60	С	PbF
	1	2	3	4	5	6	7	8
	1 -   2 -   3 -   4 -   5 -   6 -   7 -   7 -	HE) Elec Cur Pac TA : Volt Circ C =	KFRED <sup>®</sup> ctron irra rent ratio kage: = TO-22 age ration uit confi Commo	adiated ng (08 =	8 A) 600 V) : de			

Tube standard pack quantity: 50 pieces

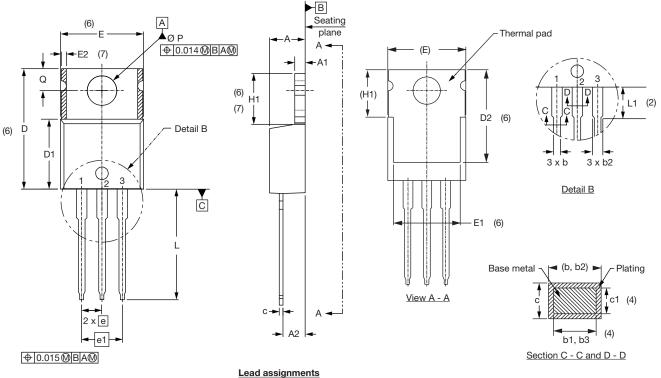
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95222					
Part marking information	www.vishay.com/doc?95225				

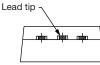


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**TO-220AB** 

#### **DIMENSIONS** in millimeters and inches





ead	assignments	
	-	

**Diodes** 

1. - Anode/open 2. - Cathode 3. - Anode

SYMBOL	MILLIMETERS INCHES		NOTES		
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

#### Notes

- <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
- <sup>(2)</sup> Lead dimension and finish uncontrolled in L1
- <sup>(3)</sup> Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed  $0.127 \text{ mm} (0.005^{\circ})$  per side. These dimensions are measured at the outermost extremes of the plastic body
- $^{\left( 4\right) }$  Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	IETERS	INCHES		NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØР	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° to 93°		

- $^{(7)}$  Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- Outline conforms to JEDEC TO-220, except A2 (maximum) and (8) D2 (minimum) where dimensions are derived from the actual package outline

Document Number: 95222 Revision: 08-Mar-11

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